

**Features:**

- n Isolated mounting base 3000V~
- n Pressure contact technology with Increased power cycling capability
- n Space and weight saving

Typical Applications

- n Inverter
- n Inductive heating
- n Chopper

V _R RM	Type & Outline
600V	MZx200-06-413F3D
800V	MZx200-08-413F3D
1000V	MZx200-10-413F3D
1200V	MZx200-12-413F3D
1400V	MZx200-14-413F3D
1600V	MZx200-16-413F3D
1800V	MZx200-18-413F3D
1800V	MZ200-18-413F3DG

MZx stands for any type of **MZC, MZA, MZK**

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T _j (°C)	VALUE			UNIT
				Min	Type	Max	
I _{F(AV)}	Mean forward current	180° half sine wave 50Hz Single side cooled, T _c =85°C	140			200	A
I _{F(RMS)}	RMS forward current					314	A
I _{RRM}	Repetitive peak current	at V _{RRM}	140			40	mA
I _{FSM}	Surge forward current	10ms half sine wave V _R =0.6V _{RRM}	140			5.5	kA
I ² t	I ² t for fusing coordination					151	A ² s*10 ³
V _{FO}	Threshold voltage		140			0.95	V
r _F	Forward slope resistance					0.90	m
V _{FM}	Peak forward voltage	I _{FM} =600A	25			1.55	V
t _{rr}	Reverse recovery time	I _{FM} =200A, t _p =4000μs, -di/dt=20A/μs, V _R =50V	140		3.0		μs
			25		2.0		μs
R _{th(j-c)}	Thermal resistance Junction to case	Single side cooled per chip				0.180	°C /W
R _{th(c-h)}	Thermal resistance case to heatsink	Single side cooled per chip				0.040	°C /W
F _m	Terminal connection torque(M8)			10.0		12.0	N·m
	Mounting torque(M6)			4.5		6.0	N·m
V _{iso}	Isolation voltage	50Hz, R.M.S, t=1min, I _{iso} : 1mA(MAX)		3000			V
T _{vj}	Junction temperature			-40		140	°C
T _{stg}	Stored temperature			-40		125	°C
W _t	Weight				770		g
Outline	413F3D						

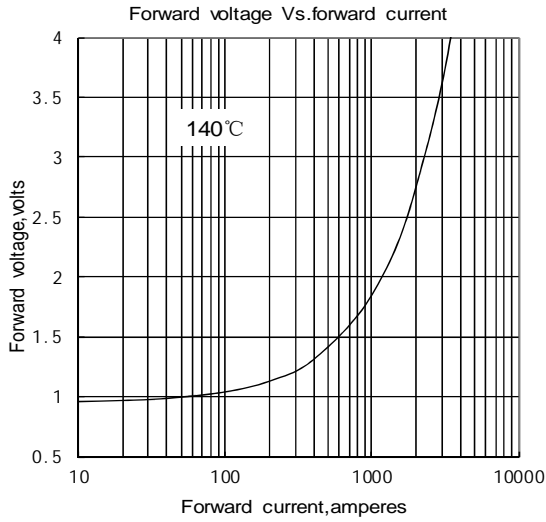


Fig.1

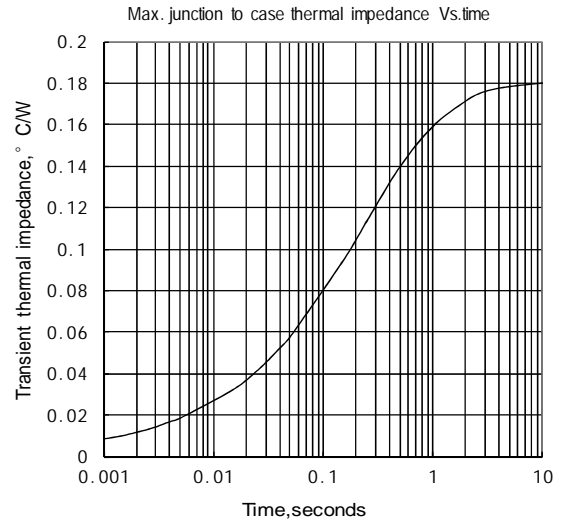


Fig.2

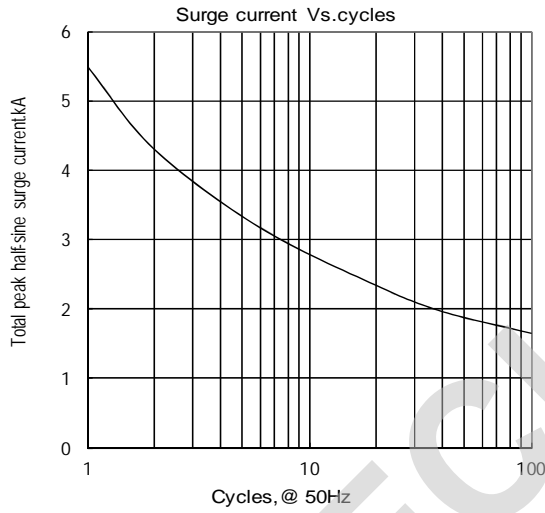


Fig.3

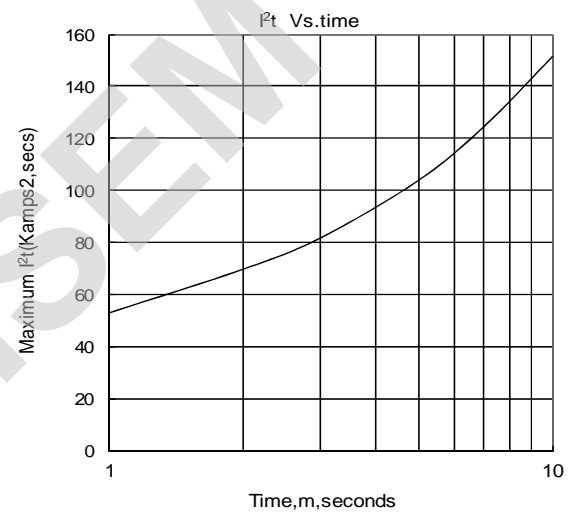
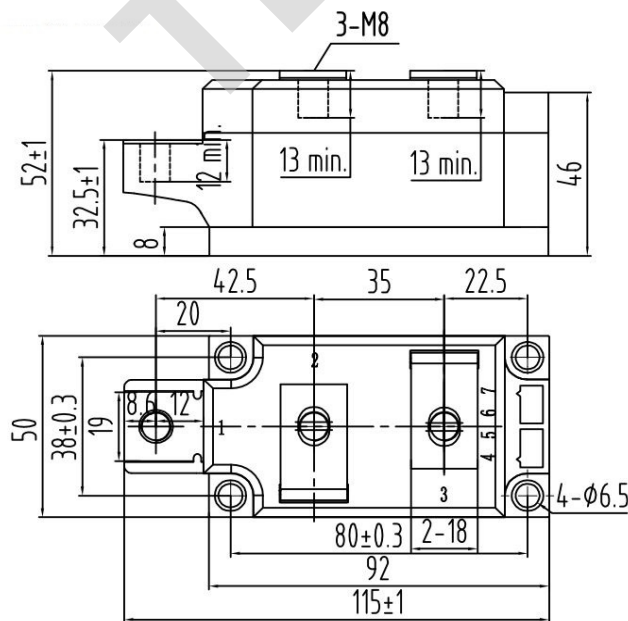
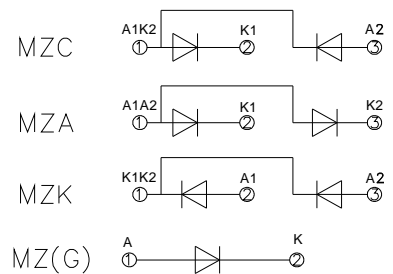


Fig.4

Outline:



Unmarked dimensional tolerance: ±0.5mm



TECHSEM reserves the right to change specifications without notice.